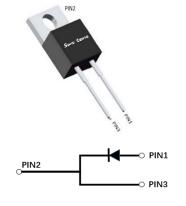


Silicon Carbide Schottky Diode

V _{RRM}	1700V
I _{F (135°C)}	18A
Q _C	143nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- Package: TO-220AC Molding compound meets UL 94 V-0 flammability rating, -, halogen-free
- Terminals: Tin plated leads
- Polarity: As marked

Maximum Ratings	(T _C =25°C Unless otherwise specified)
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PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D117010PG1
Reverse voltage (repetitive peak) @ T _j =25°C	V _{RRM}	V	1700
Reverse voltage (Surge Peak) @ T _j =25°C	V _{RSM}	V	1700
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	1700
Continuous forward current @ T _c =25°C			36
Continuous forward current @ T _c =135°C	I _F	A	18
Continuous forward current @ T _c =160°C			10
Non-repetitive peak forward surge current @ T_c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	72
Power Dissipation@ T _c =25°C	Ρτοτ	w	223
Power Dissipation@ T _c =110°C	Ртот		97
i²t Value@ T _c =25°C ,tp=10ms	∫ i²dt	A ² S	25
Operating junction and Storage temperature range	T _j ,T _{stg}	°C	-55 to +175



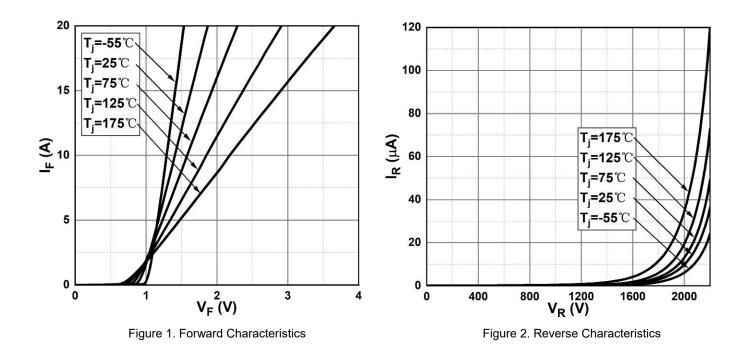
Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.											
		N	I _F =10A, T _j =25°C	1.4	1.55											
Forward voltage drop	V _F V	VF	VF	VF	V _F V	v	I _F =10A, T _j =175°C	2.2	-							
	I _R μΑ		V _R =1700V, T _j =25°C	3	18											
Reverse leakage current		μΑ	V _R =1700V, T _j =175°C	10	-											
Total capacitive charge	Qc	nC	$ \begin{array}{l} V_{R} {=} 1700 V, \ T_{j} {=} 25^{\circ} C \ , \\ Q_{C} {=} \int_{0}^{\sqrt{R}} C(V) dV \end{array} $	143	-											
	Ср	с												V _R =0V, f=1MHZ	1258	-
Total capacitance			pF	V _R =800V, f=1MHZ	64	-										
		V _R =1700V, f=1MHZ	63	-												
Capacitance Stored Energy	Ec	μJ	V _R =1700V	73	-											

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

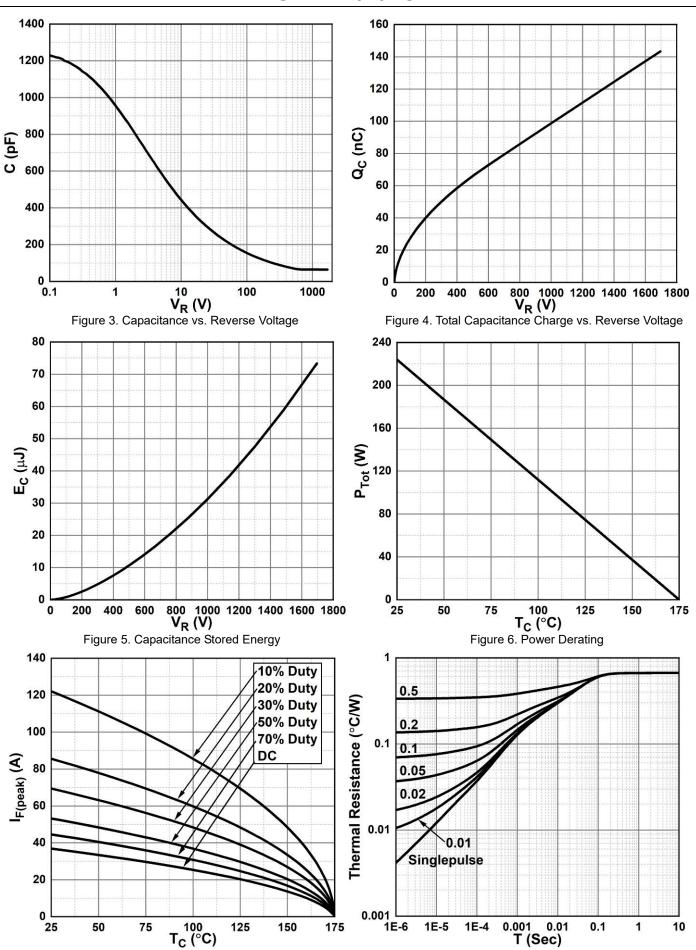
PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{_{ ext{ hetaJ-C}}}$	°C W	0.67

■Typical Characteristics



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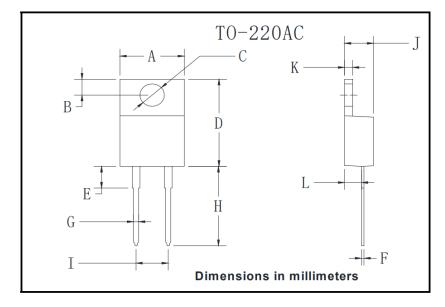
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Figure 7. Current Derating

Figure 8. Transient Thermal Impedance



Outline Dimensions



TO-220AC				
Dim	Min	Max		
А	9.95	10.35		
В	2.55	2.95		
С	3.75	4.05		
D	14.95	15.25		
E	3.75	4.25		
F	0.26	0.5		
G	0.68	0.94		
Н	13.3	13.9		
I	4.86	5.26		
J	4.38	4.78		
К	1.14	1.4		
L	2.37	2.79		

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